TOSHIBA Photocoupler GaAs Ired & Photo-Triac

TLP3061(S),TLP3062(S),TLP3063(S)

Office Machine
Household Use Equipment
Triac Driver
Solid State Relay

The TOSHIBA TLP3061 (S), TLP3062 (S) and TLP3063 (S) consist of a zero voltage crossing turn—on photo—triac optically coupled to a gallium arsenide infrared emitting diode in a six lead plastic DIP package. All parameters are tested to the specification of TLP3061, TLP3062, TLP3063.

Peak off-state voltage: 600 V (min)

• Trigger LED current: 15 mA (max) (TLP3061)

10 mA (max) (TLP3062) 5 mA(max) (TLP3063)

• On-state current: 100 mA (max)

• UL recognized: UL1577, file no. E67349

• Isolation voltage: 5000 V_{rms} (min)

• SEMKO approved: SS EN60065

SS EN60950

BSI approved: BS EN60065

BS EN60950

• Option (D4) type

VDE approved: DIN VDE0884 / 06.92

Certificate no. 68329

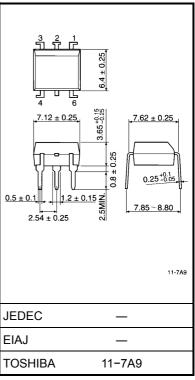
Maximum operating insulation voltage: 890 VpK Highest permissible over voltage: 8000 VpK

(Note) When a VDE0884 approved type is needed, please designate the "Option (D4)"

• Device construction

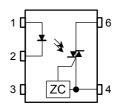
	7.62mm pich 10.16mm pi standard type (LF2) type			
Creepage distance	7.0 mm (min)	8.0 mm (min)		
Clearance	7.0 mm (min)	8.0 mm (min)		
Insulation thickness	0.5 mm (min)	0.5 mm (min)		

Unit in mm



Weight: 0.39 g

Pin Configuration(top view)



1 : Anode

2 : Cathode

3 : N.C.

4: Terminal 1

6: Terminal 2

Maximum Ratings (Ta = 25°C)

Characteristic			Symbol	Rating	Unit	
LED	Forward current	ΙF	50	mA		
	Forward current derating (Ta ≥ 53	ΔI _F / °C	-0.7	mA / °C		
	Peak forward current (100 µs pulse, 100 pps)	I _{FP}	1	А		
	Power dissipation		P _D	100	mW	
	Power dissipation derating (Ta ≥ 2	25°C)	ΔP _D / °C	-1.0	mW / °C	
	Reverse voltage		V _R	5	V	
	Junction temperature	Tj	125	°C		
	Off-state output terminal voltage	V_{DRM}	600	V		
	On-state RMS current	Ta = 25°C	l=	100	mA	
	On-state Rivis current	Ta = 70°C	I _{T(RMS)}	50	T IIIA	
	On–state current derating (Ta ≥ 25	5°C)	ΔI _T / °C	-1.1	mA / °C	
Detector	Peak on–state current (100µs pulse, 120 pps)	I _{TP}	2	Α		
De	Peak nonrepetitive surge current (P _w = 10 ms, DC = 10%)	I _{TSM}	1.2	А		
	Power dissipation	P _D	300	mW		
	Power dissipation derating (Ta ≥ 2	ΔP _D / °C	-4.0	mW / °C		
	Junction temperature	Tj	115	°C		
Storag	e temperature range		T _{stg}	-55~150	°C	
Operat	ting temperature range	T _{opr}	-40~100	°C		
Lead soldering temperature (10 s)			T _{sol}	260	°C	
Total package power dissipation			P _T	330	mW	
Total package power dissipation derating (Ta ≥ 25°C)			ΔP _T / °C	-4.4	mW / °C	
	on voltage min., R.H.≤ 60%)	BVS	5000	Vrms		

(Note 1) Device considered a two terminal device: Pins 1, 2 and 3 shorted together and pins 4 and 6 shorted together.

Recommended Operating Conditions

Characteristic	Symbol	Min.	Тур.	Max.	Unit
Supply voltage	V _{AC}	_	_	240	Vac
Forward current	I _F *	15	20	25	mA
Peak on-state current	I _{TP}	_	_	1	Α
Operating temperature	T _{opr}	-25	_	85	°C

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※ In the case of TLP3062



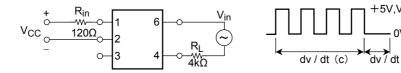
Individual Electrical Characteristics (Ta = 25°C)

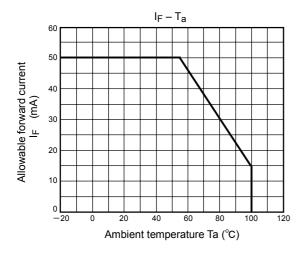
	Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
	Forward voltage	V _F	I _F = 10 mA	1.0	1.15	1.3	V
LED	Reverse current	I _R	V _R = 5 V	_	_	10	μA
	Capacitance	C _T	V = 0, f = 1 MHz	_	10	_	pF
	Peak off-state current	I _{DRM}	V _{DRM} = 600 V	_	10	1000	nA
	Peak on-state voltage	V _{TM}	I _{TM} = 100 mA	_	1.7	3.0	V
tor	Holding current	lΗ	_	_	0.6	_	mA
Detector	Critical rate of rise of off–state voltage	dv / dt	V _{in} = 240 Vrms, Ta = 85°C (Fig.:) 200	500	_	V / µs
	Critical rate of rise of commutating voltage	dv / dt (c)	V_{in} = 60 Vrms, I_T = 15mA (Fig.:) –	0.2	_	V / µs

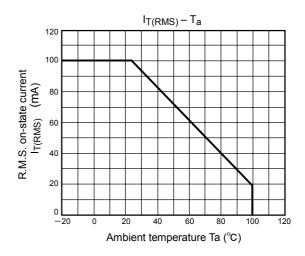
Coupled Electrical Characteristics (Ta = 25°C)

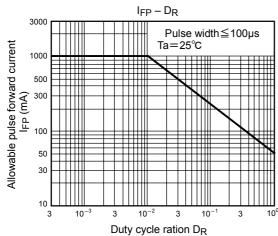
Characteristic		Symbol	Test Condition	Min.	Тур.	Max.	Unit
Trigger LED current	TLP3061	l _{FT}	V _T = 6 V	_	_	15	mA
	TLP3062			_	5	10	
	TLP3063			_	_	5	
Inhibit voltage		V _{IH}	I _F = rated I _{FT}	_	_	50	V
Leakage in inhibited state		I _{IH}	I _F = rated I _{FT} V _T = rated V _{DRM}	_	100	300	μΑ
Capacitance input to output		CS	V _S = 0, f = 1 MHz	_	0.8	_	pF
Isolation resistance		R _S	V _S = 500 V (R.H.≤ 60%)	5×10 ¹⁰	10 ¹⁴	_	Ω
			AC, 1 minute	5000	_	_	Vrms
Isolation voltage		BV_S	AC, 1 second, in oil	_	10000	_	VIIIIS
			DC, 1 minute, in oil	_	10000	_	V_{dc}

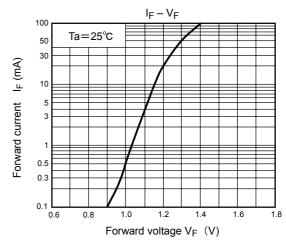
Fig. 1 dv / dt test circuit

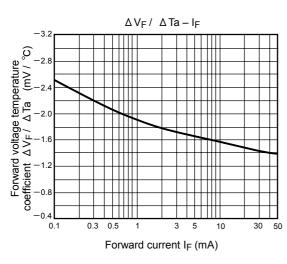


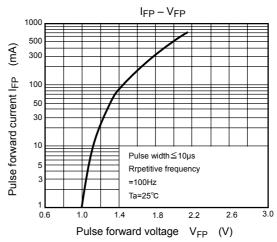




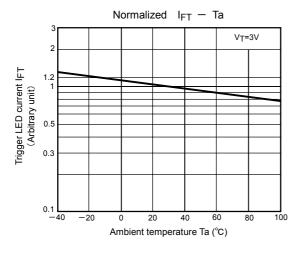


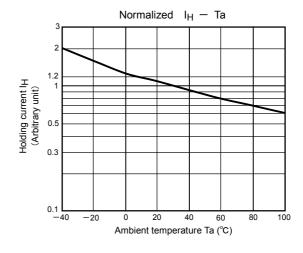


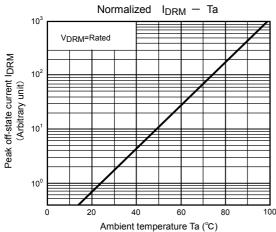


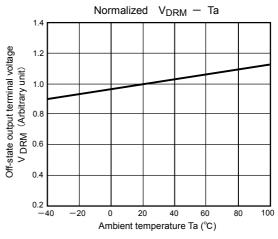


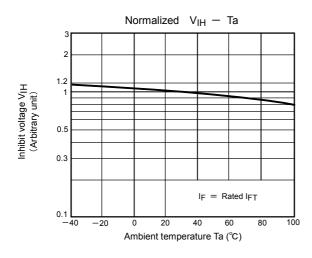
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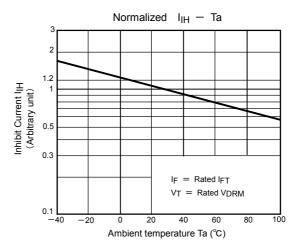












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